Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HS669A

APPLICATIONS

Low Frequancy Power Amplifier.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature····· −55~150℃

T_j——Junction Temperature····· 150℃

P_C——Collector Dissipation（T_c=25℃）····· 20W

P_C——Collector Dissipation（T_A=25℃）····· 1W

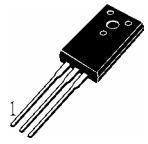
V_{CBO}——Collector-Base Voltage····· 180V

V_{CEO}——Collector-Emitter Voltage····· 160V

V_{EBO}——Emitter-Base Voltage····· 5V

I_C——Collector Current·····1.5A

TO-126



1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	180			V	I_C= 1mA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	160			V	I_C= 10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	I_E= 1mA, I_C=0
I_{CBO}	Collector Cut-off Current			10	μA	V_{CB}=160V, I_E=0
H_{FE}（1）	DC Current Gain	60		200		V_{CE}= 5V, I_C= 150mA
H_{FE}（2）	DC Current Gain	30				V_{CE}= 5V, I_C= 500mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			1	V	I_C= 500mA, I_B= 50mA
V_{BE}	Base-Emitter Voltage			1.5	V	V_{CE}=5V, I_C=150mA
ft	Current Gain-Bandwidth Product		140		MHz	V_{CE}=5V, I_C=150mA,
Cob	Output Capacitance		14		pF	V_{CB}=10V, I_E=0， f=1MHz

h_{FE} Classification

B	C
60—120	100—200